Analog Power

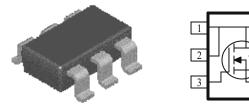
AM3454N

N-Channel 30-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- Low r_{DS(on)} provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe TSOP-6 saves board space
- Fast switching speed
- High performance trench technology

PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)} m(\Omega)$ $I_D(A)$		
30	$58 @ V_{GS} = 10V$	4.8	
	$82 @ V_{GS} = 4.5V$	4.1	



ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Units		
Drain-Source Voltage		V _{DS}	30	V		
Gate-Source Voltage			±20	v		
	$T_A=25^{\circ}C$	Τ_	4.8			
Continuous Drain Current ^a	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	ID	4.0	А		
Pulsed Drain Current ^b		I _{DM}	16			
Continuous Source Current (Diode Conduction) ^a		Is	1.25	Α		
	$T_A=25^{\circ}C$	D	2.0	W		
Power Dissipation ^a	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	LD	1.3	vv		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150	°C		

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Maximum	Units	
Maximum Junction-to-Ambient ^a	t <= 5 sec	$R_{\theta JA}$	62.5	°C/W	
	Steady-State		110	°C/W	

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

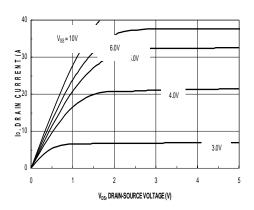
b. Pulse width limited by maximum junction temperature

			Limits			T T •4	
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = 20 V$			±100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 24 V, V_{GS} = 0 V$			1	uA	
Zero Gate Voltage Drain Current		$V_{DS} = 24 V, V_{GS} = 0 V, T_J = 55^{\circ}C$			25	uA	
On-State Drain Current ^A	I _{D(on)}	$V_{DS} = 5 V, V_{GS} = 10 V$	6			А	
Drain-Source On-Resistance ^A	r _{DS(on)}	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 4.8 \text{ A}$			58	mΩ	
Dram-Source On-Resistance		$V_{GS} = 4.5 \text{ V}, I_D = 4.1 \text{ A}$			82		
Forward Tranconductance ^A	g_{fs}	$V_{DS} = 15 \text{ V}, I_D = 4.8 \text{ A}$		6.9		S	
Diode Forward Voltage	V _{SD}	$I_{\rm S} = 2.3$ A, $V_{\rm GS} = 0$ V		0.8		V	
Dynamic ^b							
Total Gate Charge	Qg	$V_{DS} = 15 V, V_{GS} = 4.5 V,$ $I_D = 4.8 A$		2.2		nC	
Gate-Source Charge	Q _{gs}			0.5			
Gate-Drain Charge	Q _{gd}			0.8			
Turn-On Delay Time	t _{d(on)}			16			
Rise Time	t _r	V_{DD} = 25 V, R_L = 25 Ω , I_D = 1 A,		5		nS	
Turn-Off Delay Time	t _{d(off)}	$V_{\text{GEN}} = 10 \text{ V}$		23		115	
Fall-Time	t _f			3			

Notes

- a. Pulse test: $PW \le 300$ us duty cycle $\le 2\%$.
- b. Guaranteed by design, not subject to production testing.

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Typical Electrical Characteristics (N-Channel)

Figure 1. On-Region Characteristics

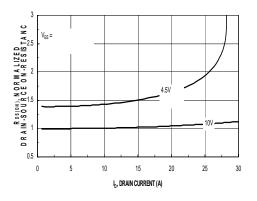


Figure 3. On Resistance Vs Vgs Voltage

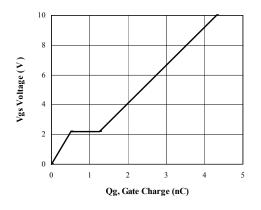


Figure 5. Gate Charge Characteristics

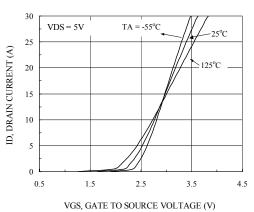


Figure 2. Body Diode Forward Voltage Variation

with Source Current and Temperature

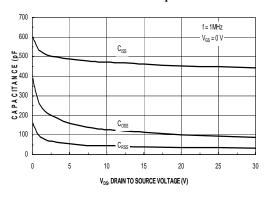


Figure 4. Capacitance Characteristics

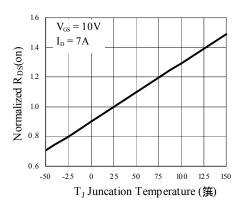
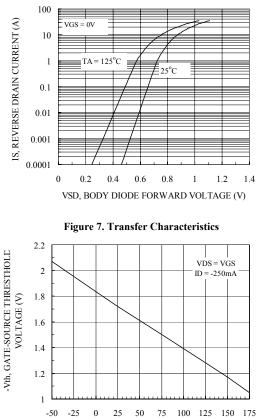


Figure 6. On-Resistance Variation with Temperature

Publication Order Number: DS-AM3454_B



Typical Electrical Characteristics (N-Channel)

TA, AMBIENT TEMPERATURE (oC)

Figure 9. Vth Gate to Source Voltage Vs Temperature

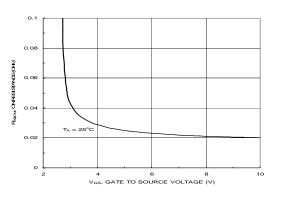


Figure 8. On-Resistance with Gate to Source Voltage

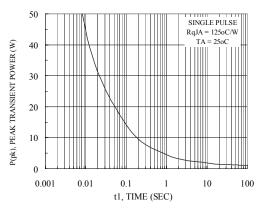
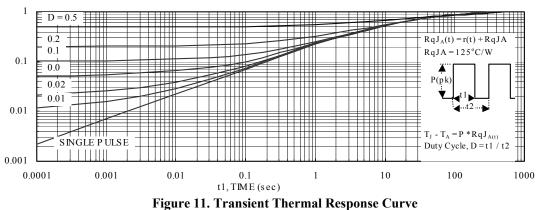


Figure 10. Single Pulse Maximum Power Dissipation



Normalized Thermal Transient Junction to Ambient

